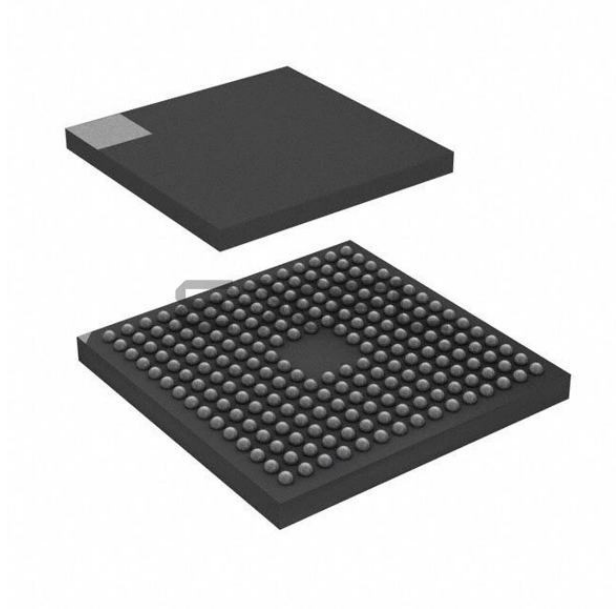

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SAI, SDIO, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	161
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	384K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	216-TFBGA
Supplier Device Package	216-TFBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f469ngh6

2.40 Analog-to-digital converters (ADCs)

Three 12-bit analog-to-digital converters are embedded and each ADC shares up to 16 external channels, performing conversions in the single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold

The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

To synchronize A/D conversion and timers, the ADCs could be triggered by any of TIM1, TIM2, TIM3, TIM4, TIM5, or TIM8 timer.

2.41 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.7 V and 3.6 V. The temperature sensor is internally connected to the same input channel as V_{BAT}, ADC1_IN18, which is used to convert the sensor output voltage into a digital value. When the temperature sensor and V_{BAT} conversion are enabled at the same time, only V_{BAT} conversion is performed.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

2.42 Digital-to-analog converter (DAC)

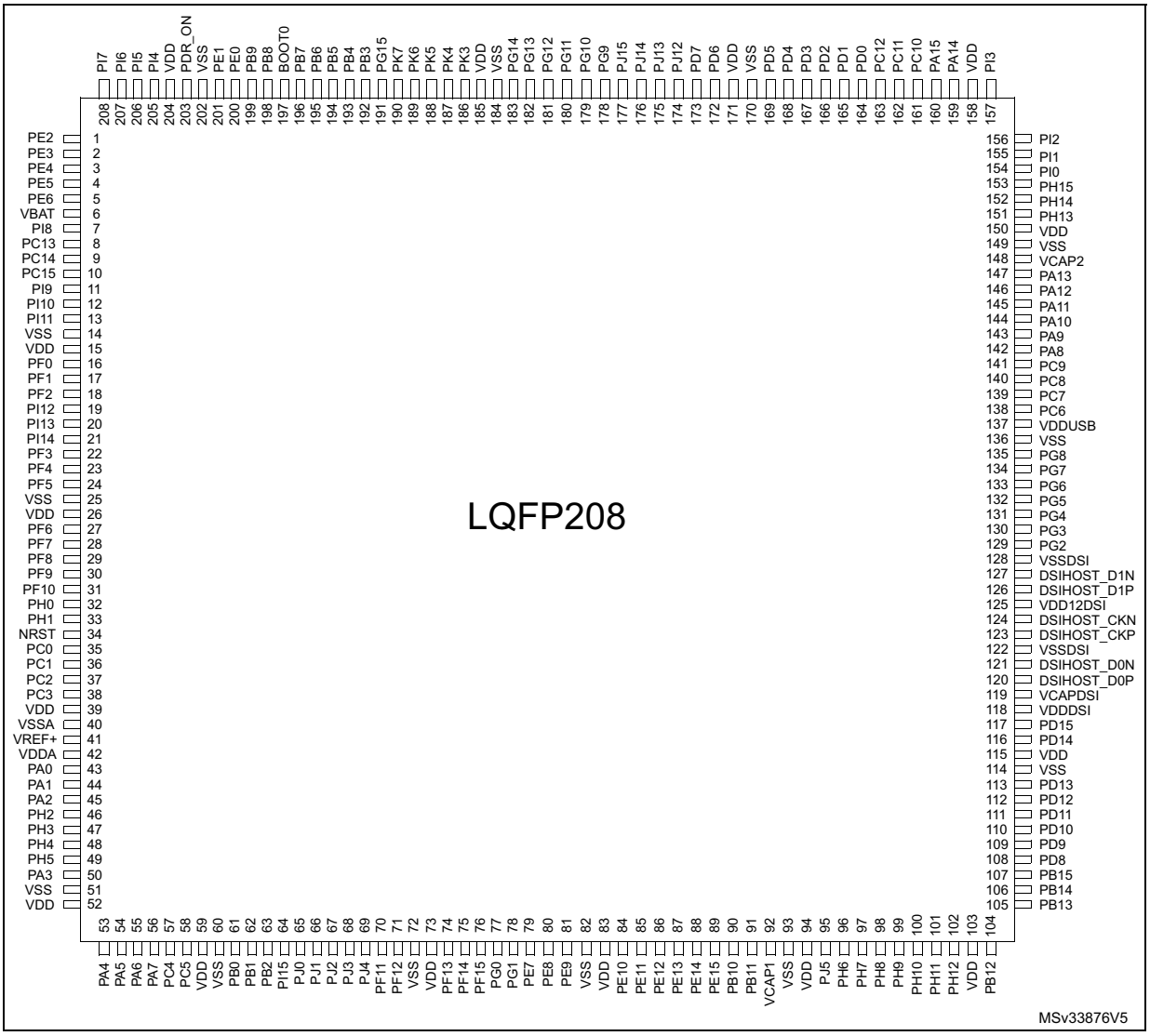
The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- 8-bit or 10-bit monotonic output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V_{REF+}

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

Figure 19. STM32F46x LQFP208 pinout



1. The above figure shows the package top view.

Table 12. Alternate function

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/2/3/4/5/6	SPI2/3/SAI1	SPI2/3/USART1/2/3	USART6/UART4/5/7/8	CAN1/2/TIM12/13/14/QUADSPI/LCD	QUADSPI/OTG2_HS/OTG1_FS	ETH	FMC/SDIO/OTG2_FS	DCMI/DSI HOST	LCD	SYS
Port A	PA0	-	TIM2_CH1/TIM2_ETR	TIM5_CH1	TIM8_ETR	-	-	-	USART2_CTS	UART4_TX	-	-	ETH_MII_CRS	-	-	-	EVENT OUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS	UART4_RX	QUADSPI_BK1_IO3	-	ETH_MII_RX_CLK/ETH_RMII_REF_CLK	-	-	LCD_R2	EVENT OUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	-	USART2_TX	-	-	-	ETH_MDIO	-	-	LCD_R1	EVENT OUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-	-	USART2_RX	-	LCD_B2	OTG_HS_ULPI_D0	ETH_MII_COL	-	-	LCD_B5	EVENT OUT
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS/I2S3_WS	USART2_CK	-	-	-	-	OTG_HS_SOF	DCMI_HSYNC	LCD_VSYNC	EVENT OUT
	PA5	-	TIM2_CH1/TIM2_ETR	-	TIM8_CH1N	-	SPI1_SCK	-	-	-	-	OTG_HS_ULPI_CK	-	-	-	LCD_R4	EVENT OUT
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-	-	DCMI_PIXCLK	LCD_G2	EVENT OUT
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-	-	TIM14_CH1	QUADSPI_CLK	ETH_MII_RX_DV/ETH_RMII_CRS_DV	FMC_SDNWE	-	-	EVENT OUT
	PA8	MCO1	TIM1_CH1	-	-	I2C3_SCL	-	-	USART1_CK	-	-	OTG_FS_SOF	-	-	-	LCD_R6	EVENT OUT
	PA9	-	TIM1_CH2	-	-	I2C3_SMBA	SPI2_SCK/I2S2_CK	-	USART1_TX	-	-	-	-	-	DCMI_D0	-	EVENT OUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-	-	DCMI_D1	-	EVENT OUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-	-	-	LCD_R4	EVENT OUT
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS	-	CAN1_TX	OTG_FS_DP	-	-	-	LCD_R5	EVENT OUT
	PA13	JTMS-SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PA14	JTCK-SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PA15	JTDI	TIM2_CH1/TIM2_ETR	-	-	-	SPI1_NSS	SPI3_NSS/I2S3_WS	-	-	-	-	-	-	-	-	EVENT ‘OUT

Table 12. Alternate function (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/2/3/4/5/6	SPI2/3/SAI1	SPI2/3/USART1/2/3	USART6/UART4/5/7/8	CAN1/2/TIM12/13/14/QUADSPI/LCD	QUADSPI/OTG2_HS/OTG1_FS	ETH	FMC/SDIO/OTG2_FS	DCMI/DSIHOST	LCD	SYS
Port J	PJ0	-	-	-	-	-	-	-	-	-	LCD_R7	-	-	-	-	LCD_R1	EVENTOUT
	PJ1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R2	EVENTOUT
	PJ2	-	-	-	-	-	-	-	-	-	-	-	-	-	DSIHOST_TE	LCD_R3	EVENTOUT
	PJ3	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R4	EVENTOUT
	PJ4	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R5	EVENTOUT
	PJ5	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_R6	EVENTOUT
	PJ12	-	-	-	-	-	-	-	-	-	LCD_G3	-	-	-	-	LCD_B0	EVENTOUT
	PJ13	-	-	-	-	-	-	-	-	-	LCD_G4	-	-	-	-	LCD_B1	EVENTOUT
	PJ14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B2	EVENTOUT
	PJ15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B3	EVENTOUT
Port K	PK3	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B4	EVENTOUT
	PK4	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B5	EVENTOUT
	PK5	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B6	EVENTOUT
	PK6	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B7	EVENTOUT
	PK7	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_DE	EVENTOUT

Table 26. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled except prefetch), regulator OFF

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ		Max(1)						Unit
				I_{DD12}	I_{DD}	T_A = 25 °C		T_A = 85 °C		T_A = 105 °C		
						I_{DD12}	I_{DD}	I_{DD12}	I_{DD}	I_{DD12}	I_{DD}	
I_{DD12} / I_{DD}	Supply current in RUN mode from V_{12} and V_{DD} supply	All Peripherals enabled(2) (3)	168	93	1	98	1	123	1	148	1	mA
			150	83	1	88	1	113	1	138	1	
			144	76	1	80	1	103	1	126	1	
			120	56	1	59	1	78	1	97	1	
			90	43	1	45	1	64	1	83	1	
			60	29	1	32	1	50	1	70	1	
			30	15	1	18	1	36	1	56	1	
			25	13	1	15	1	34	1	53	1	
		All Peripherals disabled	168	44	1	50	1	72	1	94	1	
			150	40	1	45	1	68	1	90	1	
			144	36	1	40	1	62	1	82	1	
			120	27	1	30	1	48	1	66	1	
			90	20	1	23	1	41	1	60	1	
			60	14	1	16	1	35	1	53	1	
			30	8	1	10	1	28	1	47	1	
			25	7	1	9	1	27	1	46	1	

1. Guaranteed based on test during characterization.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, DSI regulator, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

Table 31. Typical and maximum current consumption in V_{BAT} mode

Symbol	Parameter	Conditions[1]	Typ			Max[2]			Unit
			T_A = 25 °C			T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
			V_{BAT} = 1.7 V	V_{BAT}= 2.4 V	V_{BAT} = 3.3 V	V_{BAT} = 3.3 V			
I_{DD_VBAT}	Backup domain supply current	Backup SRAM ON, RTC ON and LSE oscillator in Low Power mode	1.431	1.577	1.825	1.9	12.0	24.0	µA
		Backup SRAM OFF, RTC ON and LSE oscillator in Low Power mode	0.720	0.849	1.060	1.1	7.0	13.9	
		Backup SRAM ON, RTC ON and LSE oscillator in High Drive mode	2.212	2.368	2.630	2.80	17.3	34.6	
		Backup SRAM OFF, RTC ON and LSE oscillator in High Drive mode	1.499	1.637	1.862	2.0	12.3	24.5	
		Backup SRAM ON, RTC and LSE OFF	0.710	0.720	0.760	0.8[3]	5.0	10.0[3]	
		Backup SRAM OFF, RTC and LSE OFF	0.018	0.020	0.024	0.2[3]	2.0	4.0[3]	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C_L of 6 pF for typical values.
2. Based on characterization, tested in production.
3. Based on test during characterization.

Figure 27. Typical V_{BAT} current consumption (RTC ON / backup SRAM ON and LSE in Low drive mode)

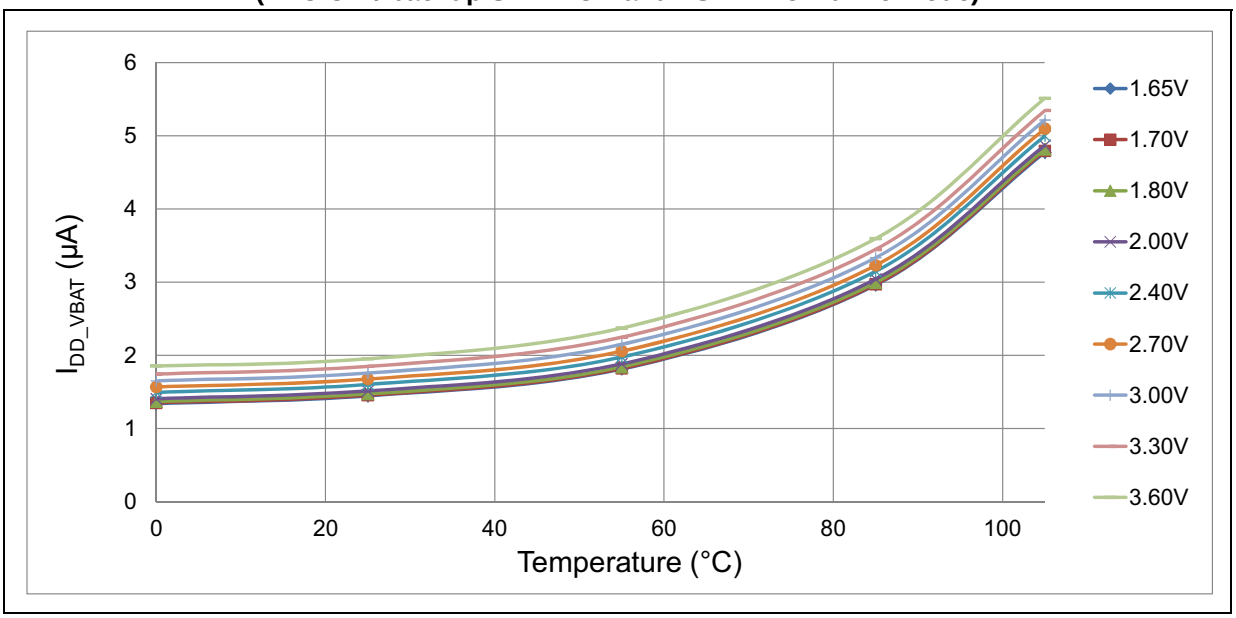
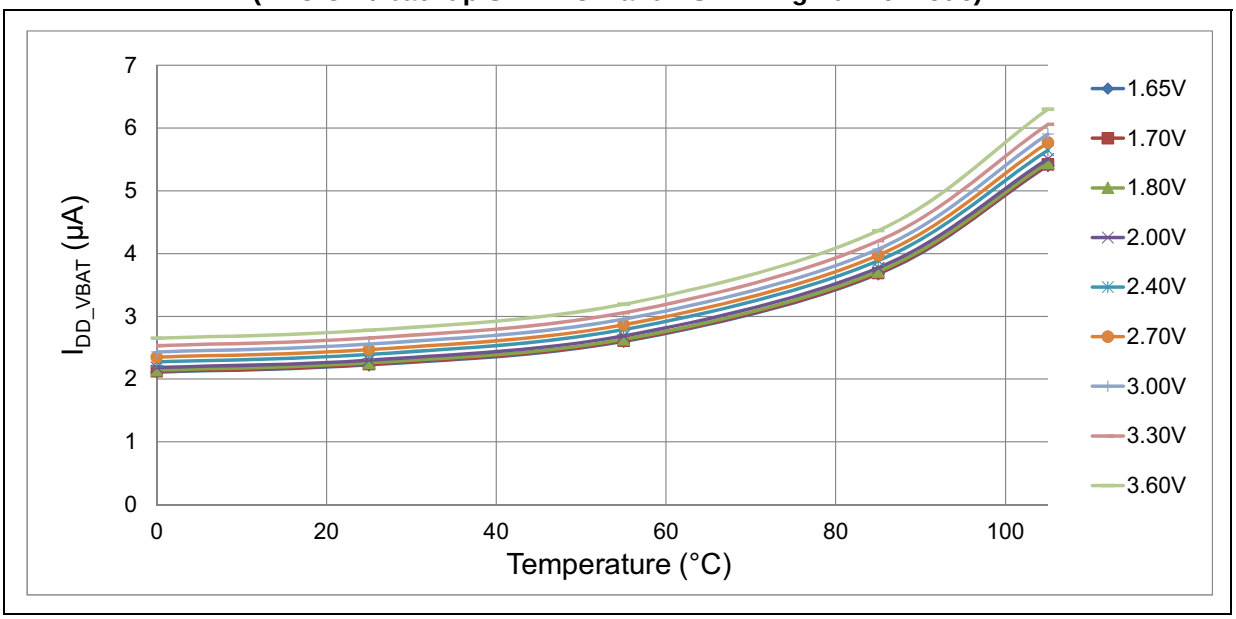


Figure 28. Typical V_{BAT} current consumption (RTC ON / backup SRAM ON and LSE in High drive mode)



I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 58: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 33*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses

5.3.12 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see *Table 54*). It is available only on the main PLL.

Table 44. SSCG parameters constraint

Symbol	Parameter	Min	Typ	Max(1)	Unit
f_{Mod}	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP	-	-	-	$2^{15} - 1$	-

1. Guaranteed by design.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$MODEPER = round[f_{PLL\_IN} / (4 \times f_{Mod})]$$

f_{PLL_IN} and f_{Mod} must be expressed in Hz.

As an example:

If f_{PLL_IN} = 1 MHz, and f_{MOD} = 1 kHz, the modulation depth (MODEPER) is given by equation 1:

$$MODEPER = round[10^6 / (4 \times 10^3)] = 250$$

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$INCSTEP = round[((2^{15} - 1) \times md \times PLLN) / (100 \times 5 \times MODEPER)]$$

f_{VCO_OUT} must be expressed in MHz.

With a modulation depth (md) = ±2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$INCSTEP = round[((2^{15} - 1) \times 2 \times 240) / (100 \times 5 \times 250)] = 126md(quantitazed)\%$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$md_{quantized}\% = (MODEPER \times INCSTEP \times 100 \times 5) / ((2^{15} - 1) \times PLLN)$$

As a result:

$$md_{quantized}\% = (250 \times 126 \times 100 \times 5) / ((2^{15} - 1) \times 240) = 2.002\%(peak)$$

Table 47. DSI-PLL characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD(PLL)}$	PLL power consumption on V_{DD12}	f_{VCO_OUT} = 500 MHz	-	0.55	0.70	mA
		f_{VCO_OUT} = 600 MHz	-	0.65	0.80	
		f_{VCO_OUT} = 1000 MHz	-	0.95	1.20	

1. Based on test during characterization.

5.3.15 MIPI D-PHY regulator characteristics

The parameters given in *Table 48* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

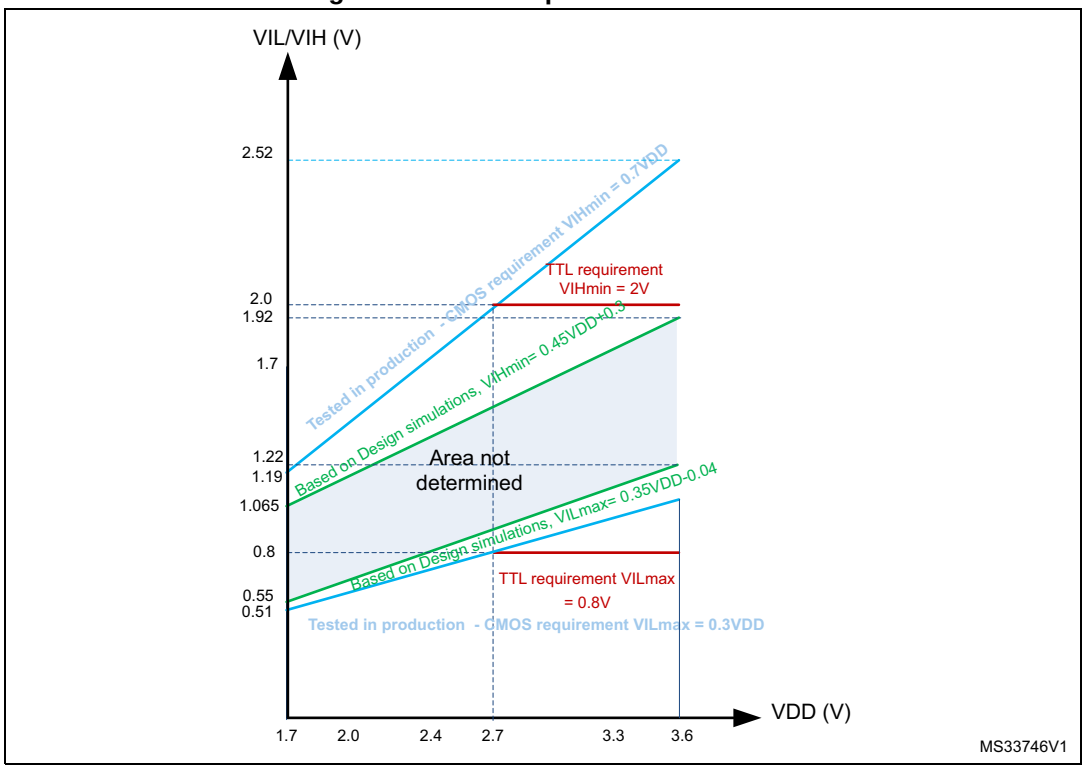
Table 48. DSI regulator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DD12DSI}$	1.2 V internal voltage on $V_{DD12DSI}$	-	1.15	1.20	1.30	V
C_{EXT}	External capacitor on V_{CAPDSI}	-	1.1	2.2	3.3	µF
ESR	External Serial Resistor	-	0	25	600	mΩ
$I_{DDDSIREG}$	Regulator power consumption	-	100	120	125	µA
I_{DDDSI}	DSI system (regulator, PLL and D-PHY) current consumption on V_{DDDSI}	Ultra Low Power Mode (Reg. ON + PLL OFF)	-	290	600	µA
		Stop State (Reg. ON + PLL OFF)	-	290	600	
$I_{DDDSILP}$	DSI system current consumption on V_{DDDSI} in LP mode communication(2)	10 MHz escape clock (Reg. ON + PLL OFF)	-	4.3	5.0	mA
		20 MHz escape clock (Reg. ON + PLL OFF)	-	4.3	5.0	
$I_{DDDSIHS}$	DSI system (regulator, PLL and D-PHY) current consumption on V_{DDDSI} in HS mode communication(3)	300 Mbps - 1 data lane (Reg. ON + PLL ON)	-	8.0	8.8	mA
		300 Mbps - 2data lane (Reg. ON + PLL ON)	-	11.4	12.5	
		500 Mbps - 1 data lane (Reg. ON + PLL ON)	-	13.5	14.7	
		500 Mbps - 2data lane (Reg. ON + PLL ON)	-	18.0	19.6	
	DSI system (regulator, PLL and D-PHY) current consumption on V_{DDDSI} in HS mode with CLK like payload	500 Mbps - 2data lane (Reg. ON + PLL ON)	-	21.4	23.3	
t_{WAKEUP}	Startup delay	C_{EXT} = 2.2 µF	-	110	-	µs
		C_{EXT} = 3.3 µF	-	-	160	
I_{INRUSH}	Inrush current on V_{DDDSI}	External capacitor load at start	-	60	200	mA

1. Based on test during characterization.
2. Values based on an average traffic in LP Command Mode.
3. Values based on an average traffic (3/4 HS traffic & 1/4 LP) in Video Mode.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in *Figure 39*.

Figure 39. FT I/O input characteristics



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14, PC15 and PI8 which can sink or source up to ±3mA. When using the PC13 to PC15 and PI8 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 5.2*. In particular:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 15*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 15*).

Table 97. Synchronous multiplexed PSRAM write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period, V_{DD} range= 2.7 to 3.6 V	$2T_{HCLK} - 1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0…2)	-	1.5	
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	T_{HCLK}	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	0	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	0	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	T_{HCLK}	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	0	
$t_{(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}-0.5$	-	
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	3	
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
$t_{d(CLKL-DATA)}$	FMC_A/D[15:0] valid data after FMC_CLK low	-	3	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	0	-	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}-0.5$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	4	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	0	-	

1. Based on test during characterization.

Figure 66. Synchronous non-multiplexed PSRAM write timings

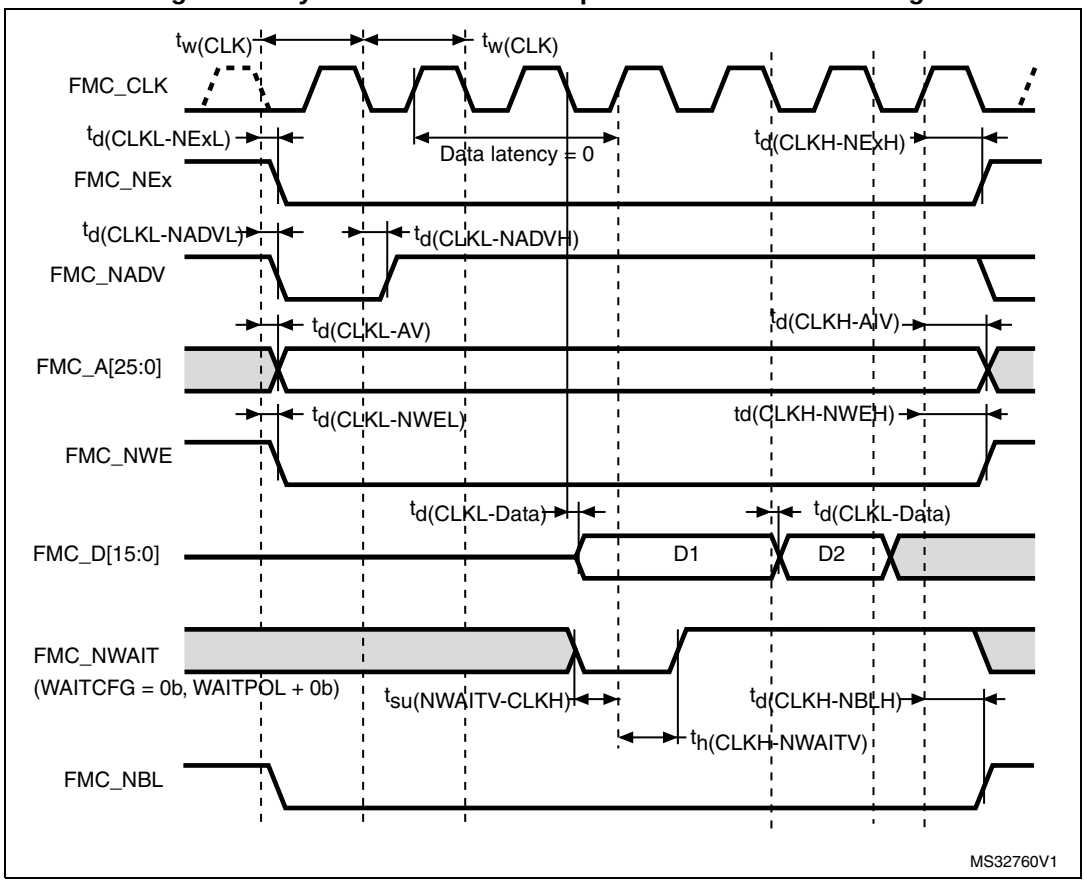


Table 99. Synchronous non-multiplexed PSRAM write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{(CLK)}$	FMC_CLK period	$2T_{HCLK} - 1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0…2)	-	0.5	
$t_{(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	T_{HCLK}	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	0	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	0	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	0	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	0	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}-0.5$	-	
$t_{d(CLKL-Data)}$	FMC_D[15:0] valid data after FMC_CLK low	-	2.5	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	0	-	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}-0.5$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	4	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	0	-	

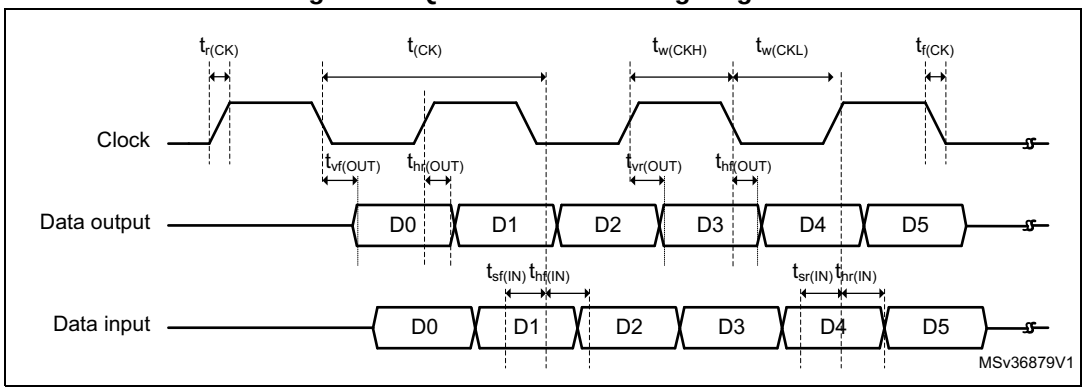
1. Based on test during characterization.

Table 107. Quad-SPI characteristics in DDR mode(1)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
F_{ck} $1/t_{(CK)}$	Quad-SPI clock frequency	2.7 V ≤ V_{DD} ≤ 3.6 V, C_L = 20 pF	-	-	80	MHz
		1.71 V ≤ V_{DD} ≤ 3.6 V, C_L = 15 pF	-	-	70	
$t_{w(CKH)}$	Quad-SPI clock high time	-	$t_{(CK)}$/2-1	-	$t_{(CK)}$/2	ns
$t_{w(CKL)}$	Quad-SPI clock low time	-	$t_{(CK)}$/2	-	$t_{(CK)}$/2+1	
$t_{sr(IN)}$ $t_{sf(IN)}$	Data input set-up time	2.7 V ≤ V_{DD} ≤ 3.6 V	2	-	-	
		1.71 V ≤ V_{DD} ≤ 3.6 V	0.5	-	-	
$t_{hr(IN)}$ $t_{hf(IN)}$	Data input hold time	2.7 V ≤ V_{DD} ≤ 3.6 V	3	-	-	
		1.71 V ≤ V_{DD} ≤ 3.6 V	4.5	-	-	
$t_{vr(OUT)}$ $t_{vf(OUT)}$	Data output valid time	DHHC=0	-	8	10.5	
		DHHC=1 Pres=1,2…	-	T_{hclk}/2+2	T_{hclk}/2+2.5	
$t_{h(OUT)}$ $t_{f(OUT)}$	Data output hold time	DHHC=0	7	-	-	
		DHHC=1 Pres=1,2…	T_{hclk}/2+0.5	-	-	

1. Guaranteed based on test during characterization.

Figure 74. Quad-SPI DDR timing diagram



5.3.31 Camera interface (DCMI) timing specifications

Unless otherwise specified, the parameters given in *Table 108* for DCMI are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage summarized in *Table 17*, with the following configuration:

- DCMI_PIXCLK polarity: falling
- DCMI_VSYNC and DCMI_HSYNC polarity: high
- Data formats: 14 bits
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 V_{DD}

Table 111. Dynamic characteristics: SD / MMC characteristics, V_{DD} = 1.71 to 1.9 V(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	f_{pp} =50 MHz	9.5	10.5	-	ns
$t_{W(CKH)}$	Clock high time		8.5	9.5	-	
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	f_{pp} =50 MHz	0.5	-	-	ns
t_{IH}	Input hold time HS		3.5	-	-	
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	f_{pp} =50 MHz	-	13.5	14.5	ns
t_{OH}	Output hold time HS		13.0	-	-	

1. Guaranteed based on test during characterization.
2. C_{load} = 20 pF.

5.3.34 RTC characteristics

Table 112. RTC characteristics

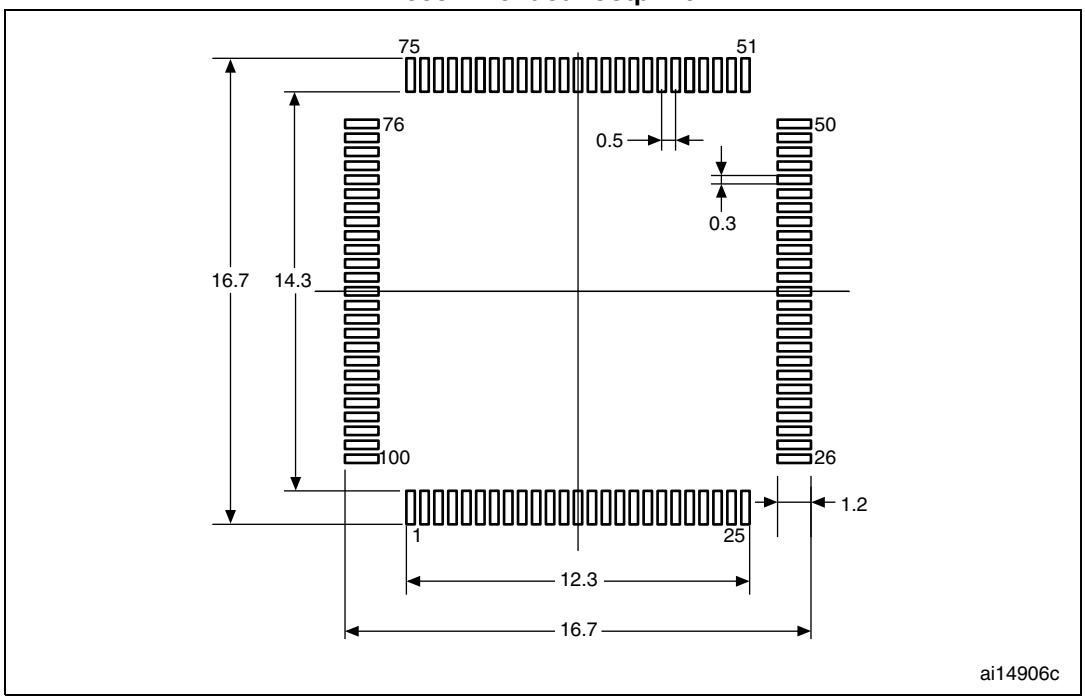
Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1}/RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

Table 113. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 81. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint

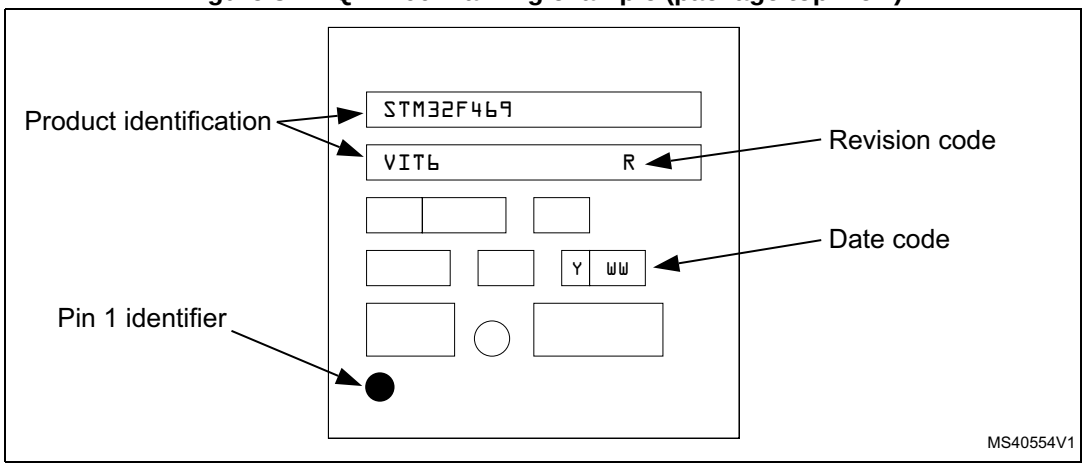


1. Dimensions are expressed in millimeters.

Device Marking for LQFP100

The following figure gives an example of topside marking orientation versus pin 1 identifier location. Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 82. LQFP100 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

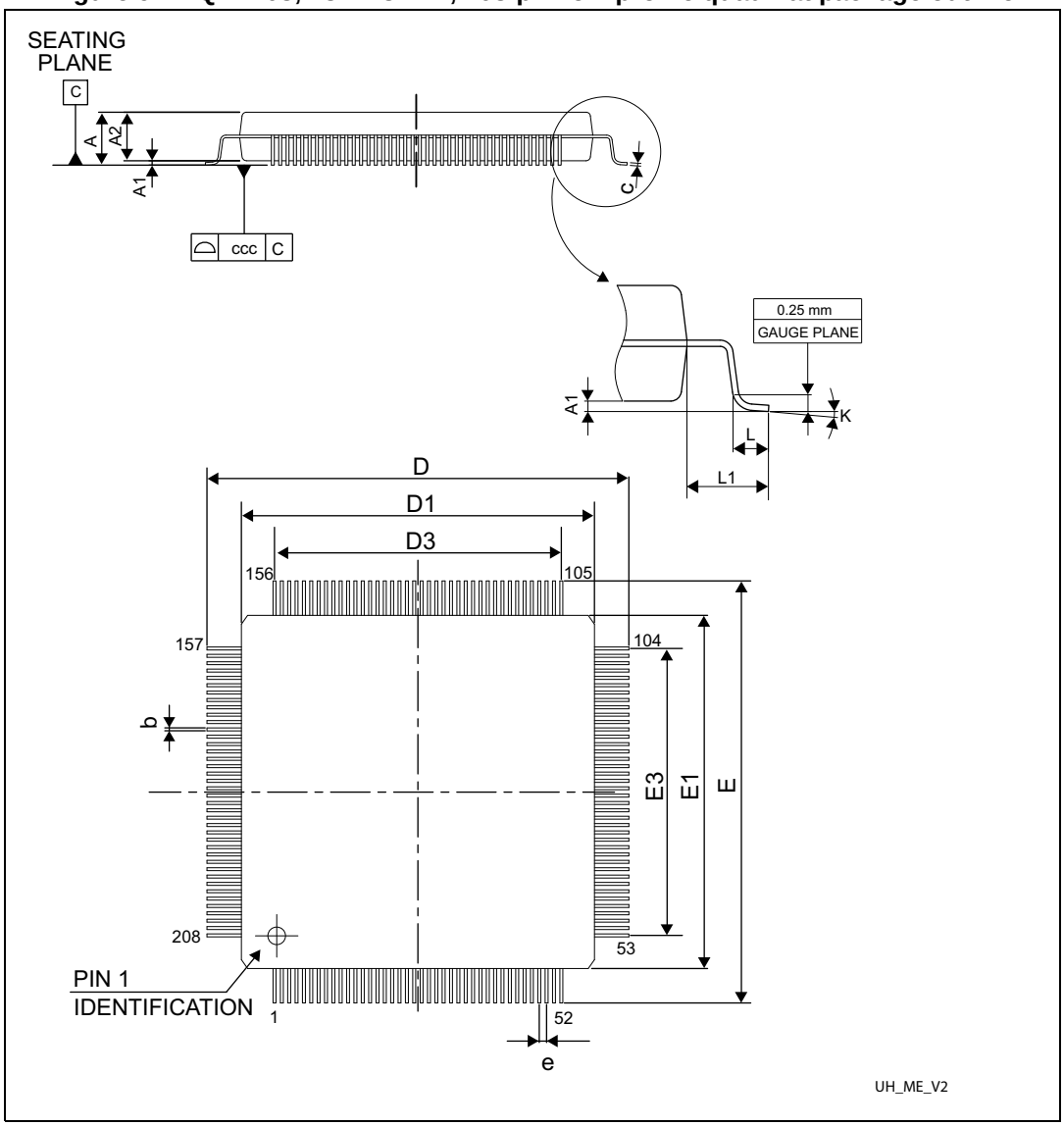
Table 115. WLCSP168 - 168-pin, 4.891 x 5.692 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.170	-	-	0.0067	-
A2	-	0.380	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
b[3]	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	4.856	4.891	4.926	0.1912	0.1926	0.1939
E	5.657	5.692	5.727	0.2227	0.2241	0.2255
e	-	0.400	-	-	0.0157	-
e1	-	4.400	-	-	0.1732	-
e2	-	5.200	-	-	0.2047	-
F	-	0.2455	-	-	0.0097	-
G	-	0.246	-	-	0.0097	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

6.7 LQFP208 package information

Figure 94. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package outline



1. Drawing is not to scale.

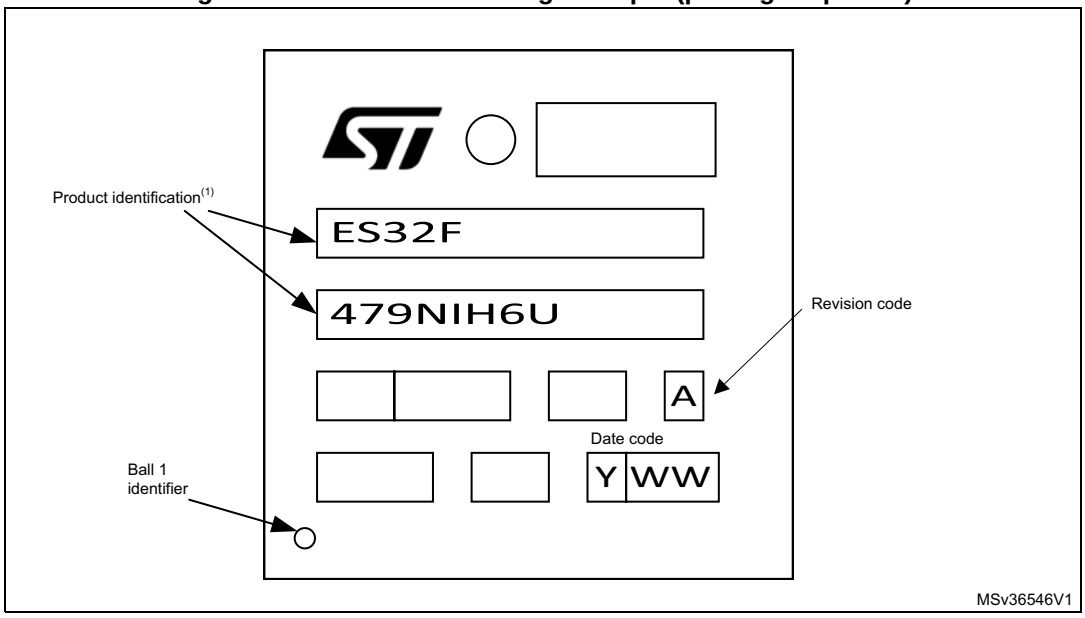
Table 120. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	--	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106

Device Marking for TFBGA216

The following figure gives an example of topside marking orientation versus ball A1 identifier location. Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 98. TFBGA216 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.9 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max x Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$P_{I/O}$ max = Σ (V_{OL} × I_{OL}) + Σ((V_{DD} – V_{OH}) × I_{OH}),

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 122. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP100	43	°C/W
	Thermal resistance junction-ambient LQFP144	40	
	Thermal resistance junction-ambient WLCSP168	31	
	Thermal resistance junction-ambient LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	
	Thermal resistance junction-ambient LQFP208 - 28 × 28 mm / 0.5 mm pitch	19	
	Thermal resistance junction-ambient UFBGA169 - 7 × 7mm / 0.5 mm pitch	52	
	Thermal resistance junction-ambient UFBGA176 - 10 × 10 mm / 0.5 mm pitch	39	
	Thermal resistance junction-ambient TFBGA216 - 13 × 13 mm / 0.8 mm pitch	29	

Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.